

AMENDMENT

In the specification

Please amend paragraph 0026 (the paragraph that spans page 8, lines 3-16) as follows:

In FIG. 1D, after the InP regrowth layer 135 has been grown and the dielectric film 120 removed, a ferric chloride etch is applied to the layer structure 100, thus removing the sacrificial InGaAs layers 108a, 108b and 108c that were defined in the first growth shown above in FIG. 1A. The removal of the InGaAs sacrificial material leaves air gaps 110a, 110b and 110c in the areas vacated by the removal of the InGaAs sacrificial material 108a, 108b and 108c. In accordance with an aspect of the invention, the InP regrowth layer 135 acts as a mechanical support layer that supports the remaining layers 106a, 106b, 106c and 106d of the InP semiconductor material. The InP regrowth layer 135 maintains the layer thickness of the air gaps 110a, 110b and 110c following the removal of the sacrificial InGaAs layers defined in the first growth. The airgaps 110a ~~110a~~, 110b and 110c may also be filled with other substances that provide a high index contrast with the layers of material at the gap/semiconductor interface. Such a substance may include, for example, an inert gas such as helium or nitrogen.